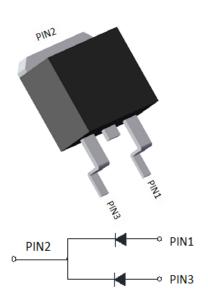




Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260°C

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

DAD ANTERD COMPANY AND			MDDD1 00/5007
PARAMETER	SYMBOL	UNIT	MBRBL20150CT
Device marking code			MBRBL20150CT
Repetitive Peak Reverse Voltage	V_{RRM}	V	150
Average Rectified Output Current @60Hz sine wave, R-load, Ta (FIG 1)	Io	А	20
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	I _{FSM}	А	160
Current Squared Time @1ms≤t≤8.3ms Tj=25℃,rating of per diode	l ² t	A ² s	106
Storage Temperature	T_{stg}	°C	-55 ~ + 150
Junction Temperature	Tj	°C	-55 ~ + 150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL20150CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	٧	I _{FM} =10.0A	0.84
Maximum DC reverse current at	I _{RRM1}	mA	V _{RM} =V _{RRM} Ta=25°C	0.1
rated DC blocking voltage per diode	I _{RRM2}		V _{RM} =V _{RRM} Ta=100℃	20

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBRBL20150CT	
	Thermal Resistance	Between junction and case	$R_{ heta J ext{-}C}$	°C/W	2.0



MBRBL20150CT

■Ordering Information (Example)

PREFERED P/N	ED P/N UNIT WEIGHT(g) MINIIMUM INNER BOX PACKAGE(pcs) QUANTITY(pcs)			OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRBL20150CT	Approximate 1.43	50	2000	8000	Tube
MBRBL20150CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

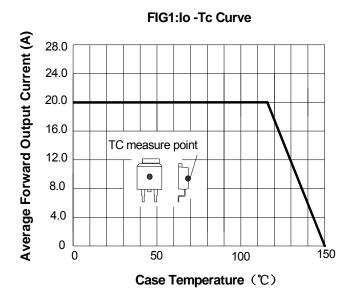
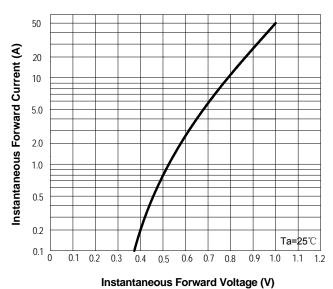


FIG2:Surge Forward Current Capability 240 Peak Forward Surge Current (A) 200 160 8.3ms Single Half Sine-Wave 120 JEDEC Method 80 40 0 2 10 50 100 **Number of Cycles**

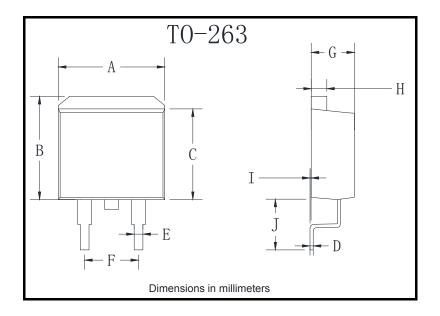
FIG3: Forward Voltage





MBRBL20150CT

■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		



MBRBL20150CT

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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